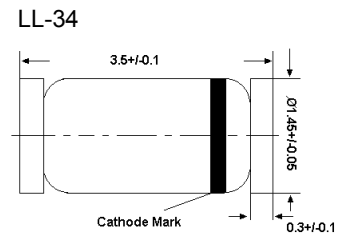


BAV101~BAV103



Silicon Epitaxial Planar Diodes

High Voltage Switching Diodes



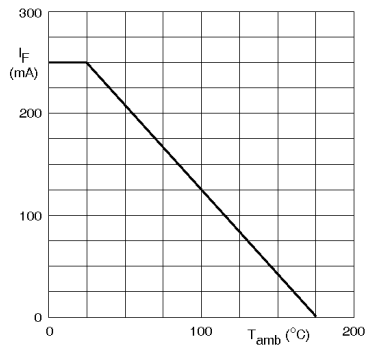
Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
		200	
		250	
Reverse Voltage	V_R	100	V
		150	
		200	
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1	A
		3	
		9	
Total Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

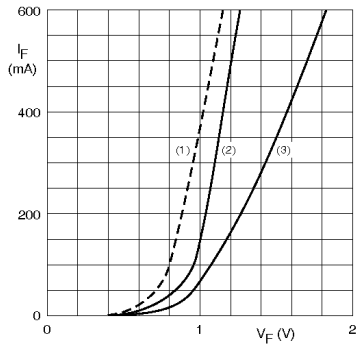
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	1	V
		1.25	
Reverse Current	I_R	100	nA
		100	nA
		100	nA
		100	μA
		100	μA
		100	μA
Diode Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_d	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}$, $I_{rr} = 3\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	50	ns



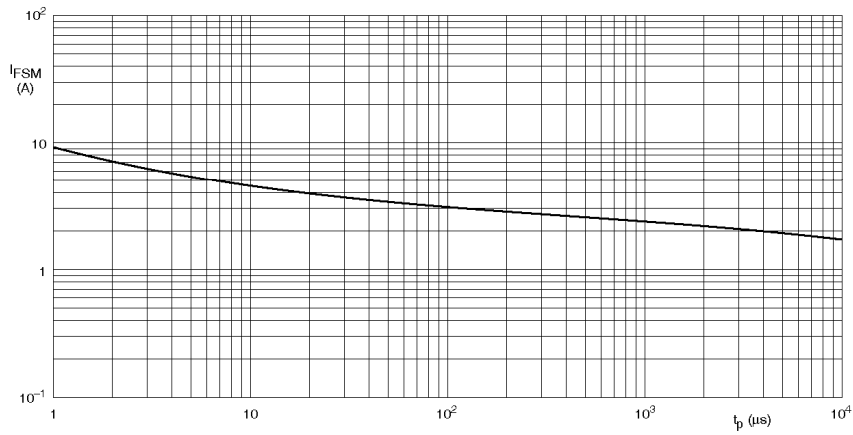
Device mounted on an FR4 printed-circuit board.

Maximum permissible continuous forward current as a function of ambient temperature.



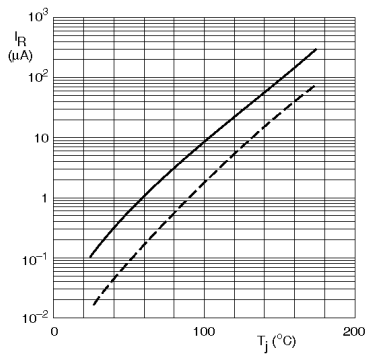
- (1) $T_J = 150$ °C; typical values.
- (2) $T_a = 25$ °C; typical values.
- (3) $T_a = 25$ °C; maximum values.

Forward current as a function of forward voltage.



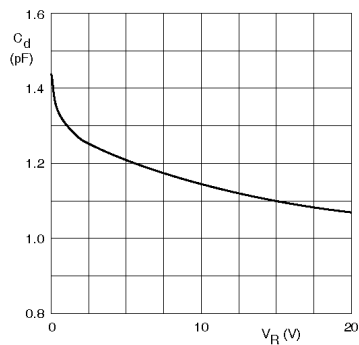
Based on square wave currents.
 $T_a = 25$ °C prior to surge.

Maximum permissible non-repetitive peak forward current as a function of pulse duration.



$V_R = V_{Rmax}$.
Solid line; maximum values.
Dotted line; typical values.

Reverse current as a function of junction temperature.



$f = 1$ MHz; $T_J = 25$ °C.

Diode capacitance as a function of reverse voltage; typical values.